



### 40V COMPLEMENTARY NPN-PNP SMALL SIGNAL TRANSISTOR IN SOT363

#### **Features**

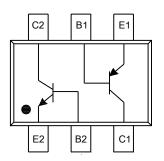
- Complementary Pair One 3904-Type NPN
  One 3906-Type PNP
- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (MMDT3946Q)

#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.006 grams (Approximate)



Top View



E1, B1, C1 = PNP 3906 E2, B2, C2 = NPN 3904

Device Schematic and Pinout Top View

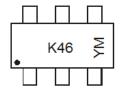
### **Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT3946-7-F	AEC-Q101	K46	7	8	3,000
MMDT3946-7R-F	AEC-Q101	K46	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



K46 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2018		2019	2020		2021	2022		2023	2024		2025
Code	F		G	Н			J		K	L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### Absolute Maximum Ratings, NPN 3904 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	200	mA

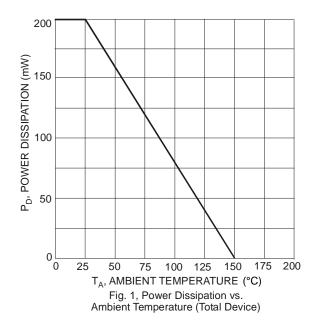
## Absolute Maximum Ratings, PNP 3906 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	Ic	-200	mA

### Thermal Characteristics, Total Device (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. For a device mounted on minimum recommended pad layout that is on a single-sided 0.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.





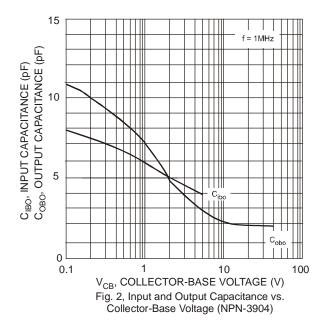
## Electrical Characteristics, NPN 3904 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

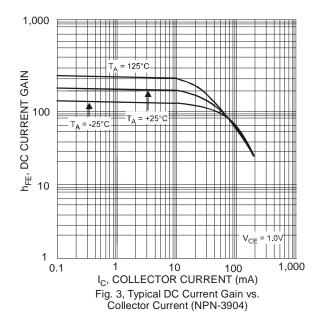
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60		٧	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_CEO$	40		>	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0		>	$I_E = 10\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current	$I_{BL}$		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 6)					
Static Forward Current Transfer Ratio	h <sub>FE</sub>	40 70 100 60 30	 300  		$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_C &= 10 m A, \ V_{CE} = 1.0 V \\ I_C &= 50 m A, \ V_{CE} = 1.0 V \\ I_C &= 100 m A, \ V_{CE} = 1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.20 0.30	٧	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	٧	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	$C_{ibo}$	_	8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA,
Small Signal Current Gain	h <sub>fe</sub>	100	400		f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300		MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 100MHz
Noise Figure	NF		5.0	dB	$V_{CE} = 5.0V, I_{C} = 100\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Fall Time	t <sub>f</sub>	_	50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$

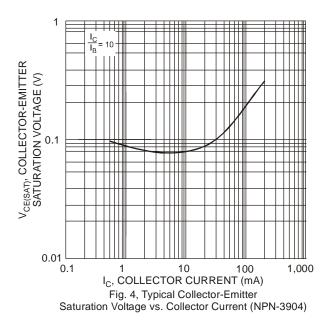
Notes: 6. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

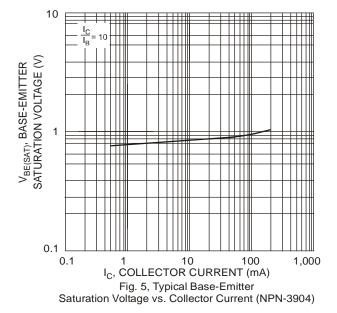


### Typical Electrical Characteristics, NPN 3904 (@TA = +25°C, unless otherwise specified.)











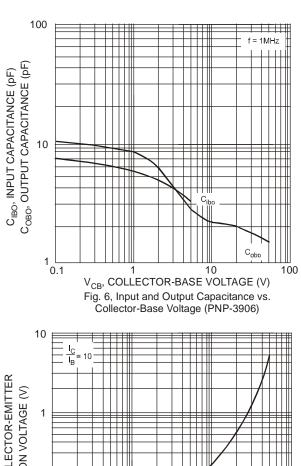
## Electrical Characteristics, PNP 3906 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-40		V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>	1	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Base Cutoff Current	I <sub>BL</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 6)					
Static Forward Current Transfer Ratio	h <sub>FE</sub>	60 80 100 60 30	300 — —	_	$\begin{split} I_C &= -100 \mu A,  V_{CE} = -1.0 V \\ I_C &= -1.0 m A,  V_{CE} = -1.0 V \\ I_C &= -10 m A,  V_{CE} = -1.0 V \\ I_C &= -50 m A,  V_{CE} = -1.0 V \\ I_C &= -100 m A,  V_{CE} = -1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		-0.25 -0.40	V	$I_C = -10$ mA, $I_B = -1.0$ mA $I_C = -50$ mA, $I_B = -5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	_	4.5	pF	$V_{CB} = -5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	$C_{ibo}$		10	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_C = 0$
Input Impedance	h <sub>ie</sub>	2.0	12	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	$V_{CE} = -10V, I_{C} = -1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400		f = 1.0kHz
Output Admittance	h <sub>oe</sub>	3.0	60	μS	
Current Gain-Bandwidth Product	f⊤	250	_	MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE} = -5.0V$ , $I_{C} = -100\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$
SWITCHING CHARACTERISTICS			•	•	•
Delay Time	t <sub>d</sub>		35	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA,
Rise Time	t <sub>r</sub>		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t <sub>f</sub>	_	75	ns	$I_{B1} = -I_{B2} = -1.0 \text{mA}$

Notes: 6. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



## Typical Electrical Characteristics, PNP 3906 (@T<sub>A</sub> = +25°C, unless otherwise specified.)



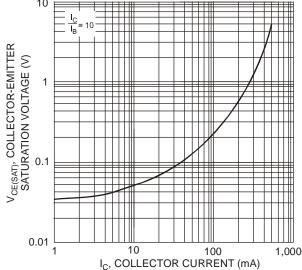
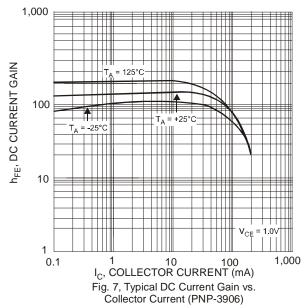


Fig. 8, Typical Collector-Emitter Saturation Voltage vs. Collector Current (PNP-3906)



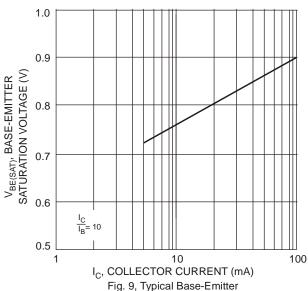
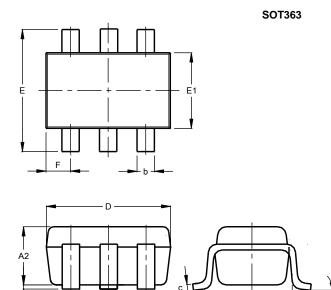


Fig. 9, Typical Base-Emitter Saturation Voltage vs. Collector Current (PNP-3906)



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

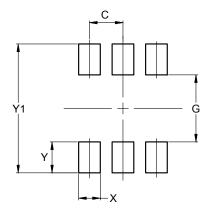


SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.10	0.30	0.25				
C	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	.650 E	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



Dimensions	Value (in mm)			
С	0.650			
G	1.300			
X	0.420			
Y	0.600			
V1	2 500			



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